

isc Silicon NPN Power Transistor

BUS50

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 125V(\text{Min})$
- High Current Capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

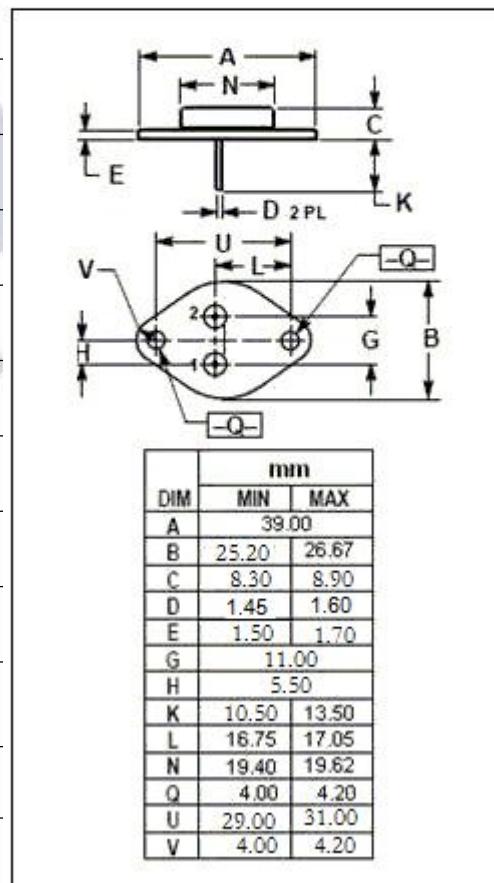
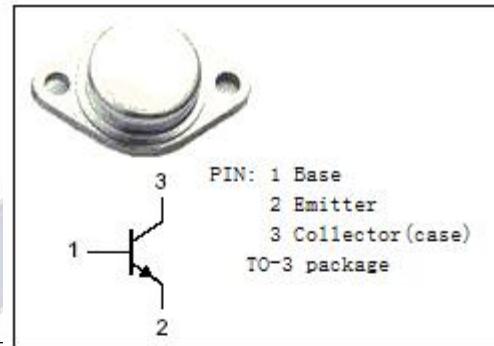
- Designed for low voltage ,high speed,power switching in Inductive circuits where fall time is critical.It is particularly suited for battery switch mode application such as switching regulations.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	125	V
V_{EBO}	Emitter-Base Voltage	7	V
I_c	Collector Current-Continuous	70	A
I_b	Base Current-Continuous	20	A
P_c	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	350	W
T_j	Junction Temperature	-65~200	°C
T_{stg}	Storage Temperature	-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Thermal Resistance,Junction to Case	0.5	°C/W



isc Silicon NPN Power Transistor**BUS50****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C =50mA ; I _B = 0	125			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 35A; I _B = 2A			1.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 70A; I _B = 7A			1.2	V
V _{BE(sat)-1}	Base-Emitter Saturation Voltage	I _C = 35A; I _B = 2A			1.8	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _C = 70A; I _B =7A			2.0	V
I _{CEO}	Collector Cutoff Current	V _{CE} = 125V; I _B = 0			1.0	mA
I _{CBO}	Collector Cutoff Current	V _{CB} = 200V; I _E = 0 V _{CB} = 200V; I _E = 0; T _c = 125°C			0.2 2	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7V; I _C =0			0.2	mA
h _{FE-1}	DC Current Gain	I _C = 5A ; V _{CE} = 4V	20			
h _{FE-2}	DC Current Gain	I _C = 50A ; V _{CE} = 4V	15			